Features

Speech Circuit

- Adjustable DC Characteristic
- Symmetrical Input of Microphone Amplifier
- Receiving Amplifier for Dynamic or Piezo-electric Earpieces
- Automatic Line-loss Compensation

Dialer

- DTMF/Pulse Switchable
- Pulse Dialing 66/33 or 60/40 or DTMF Dialing Selectable by Pin
- Selectable Flashing Duration by Key Pad
- Pause Function
- Optical Indication of Temporary DTMF Mode
- Keytone for Pulse Dialing
- Last Number Redial up to 32 Digits
- Three by 17 Digits Direct (One-touch) Memory
- Ten by 17 Digits Indirect (Two-touch) Memory
- Notice Function up to 32 Digits
- Standard Low-cost Crystal 3.58 MHz or Ceramic Resonator
- Handset Mute (Privacy) with Optical Indication
- Additional Toggle Flipflop
- Internal Loop Interrupt Detection

Tone Ringer

- 2-tone Ringer
- Adjustable Volume
- RC Oscillator
- Adjustable Threshold

Benefits

- Low Number of External Components
- High Quality through One IC Solution

Electrostatic sensitive device. Observe precautions for handling.



Description

Atmel's low-voltage telephone circuit U3761MB-T performs all the speech and line interface functions required in an electronic telephone set, a tone ringer, a pulse and DTMF dialing with redial, notice function, and 13 memories. Operation below 15 mA is possible with reduced performance.



Universal Telephone IC -All Functions Integrated

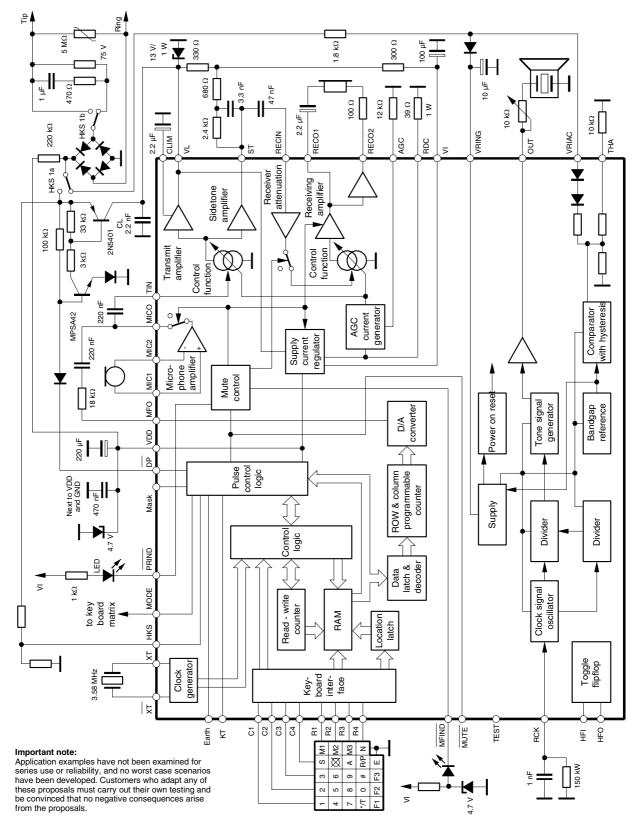
U3761MB-T

Rev. 4744A-CORD-09/03





Figure 1. Block Diagram

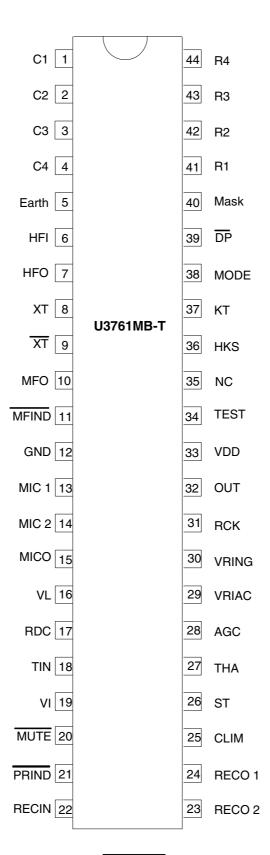


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Pin Configuration

Figure 2. Pinning SSO44





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Pin Description

Pin	Symbol	Function	Configuration
1	C1		
2	C2		
4	C3 C4	Keyboard input	C1 PD PD PD C2-C4 PD PD PD PD PD PD PD PD PD PD PD
5	Earth	Earth key (604 ms high pulse, 1 s pause)	EARTH
6	HFI	Toggle flipflop input Input with 200 kΩ pull-down resistor HFI triggers HFO with each LOW/HIGH edge	
7	HFO	Output will be toggled by each LOW/HIGH edge at HFI	HFO B

Pin	Symbol	Function	Configuration
8 9	хт хт	A built-in inverter provides oscillation with an inexpensive 3.579545-MHz crystal or ceramic resonator	XT VDD VDD PD VDD VDD VDD VDD VDD
10	MFO	$\begin{array}{c c} \text{Output of DTMF} \\ \text{DTMF output frequency} \\ \text{Specified (Hz) Actual (Hz) Error (%)} \\ \text{R}_1 & 697 & 699 & +0.28 \\ \text{R}_2 & 770 & 766 & -0.52 \\ \text{R}_3 & 852 & 848 & -0.47 \\ \text{R}_4 & 941 & 940 & -0.10 \\ \text{C}_1 & 1209 & 1216 & +0.57 \\ \text{C}_2 & 1336 & 1332 & -0.30 \\ \text{C}_3 & 1477 & 1472 & -0.34 \\ \end{array}$	
11	MFIND	During the temporary DTMF mode the output switches to low Reset by on hook condition Maximum voltage at MFIND = 5.5 V	MFIND MFIND
12	GND	Ground	
13 14	MIC 1 MIC 2	Inverting input of microphone amplifier Non-inverting input of microphone amplifier	MIC1





Pin	Symbol	Function	Configuration
15	MICO	Transmit pre-amp output which is normally capacitively coupled to Pin TIN	MICO
16	VL	Positive supply voltage input to the device. The current through this pin is modulated by the transmit signal.	VL PD RDC PD PD PD PD PD PD PD PD PD PD PD PD PD
17	RDC	An external resistor (1 W) is required from this pin to GND to control the DC input impedance of the circuit. It has a nominal value of 39 Ω for low-voltage operation. Values up to 100 Ω may be used to increase the available transmit output voltage swing at the expense of low-voltage operation.	AGC
18	TIN	Input to the line output driver amplifier. Transmit AGC applied to this stage.	TIN PD 16 V
19	Vı	This internal voltage bias line must be connected to VL via an external resistor which dominates the AC input impedance of the circuit and should be 680 Ω for an 600- Ω input impedance or 1.2 k Ω for a 900- Ω input impedance.	VI PD

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Pin	Symbol	Function	Configuration
20	MUTE	Pin for testing Forcing MUTE to GND mutes the microphone and decreases the earpiece signal by typically 29 dB; no pull up circuit allowed	
21	PRIND	PRIVACY indication pin Open collector with minimum 1 mA drive current to GND when PRIVACY = active	
22	RECIN	Receive amplifier input. The receiving amplification is regulated by an AGC.	RECIN 60K
23 24	RECO2 RECO1	Output of the receive amplifier. Dynamic transducers with a minimum impedance of 100 Ω can be directly driven by these outputs.	RECO2 RECO1
25	CLIM	Time constant of anticlipping in transmit path. CLIM $\ge 2.2 \ \mu F$ CLIM = GND: anticlipping inactive	
26	ST	The output of the sidetone cancellation signal, which requires a balanced impedance of 8 to 10 times the subscriber's line impedance to be connected to pin VL.	ST PD PD PD





Pin	Symbol	Function	Configuration
27	THA	Ringer threshold adjustment	$\mathbf{PD} = \mathbf{PD} = PD$
28	AGC	The range of transmit and receive gain variations between short and long loops may be adjusted by connecting a resistor R_{AGC} from this pin to (GND). This pin can be left open to set AGC out of action.	AGC
29	VRIAC	Ringing supply	
30	VRING	DC supply voltage for the tone ringer is limited to 30 V with integrated Z-diode.	VRING PD 90 00T PD 50 V PD 50 V
31	RCK	RC clock oscillator for ringer	RCK

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Pin	Symbol	Function	Configuration
32	OUT	Buzzer output	VRING PD B OUT PD S OUT PD S OUT
33	VDD	Supply output for dialer part	
34	Test	Test input with 6.25 k Ω pull-up resistor	TEST P
35	NC	Not connected	
36	HKS	Hook switch input HKS = 0: On-hook state. Chip in sleep mode, no operation (external pull-down resistor recommended) HKS = 1: Off-hook state. Chip enable for normal operation $I_{HKS} \le 0.5$ mA	HKS P
37	кт	Keytone output signal which is sent out in pulse dialing mode with a keytone frequency of 582 Hz. KT sink/drive current is about 100 μA at V _{DD} = 2.5 V	





Pin	Symbol	Function	Configuration
38	MODE	Pulling MODE pin to: C3: tone mode with 87 ms burst time and 140 ms pause C4: tone mode with 87 ms DTMF burst and 87 ms pause R1: pulse mode with 20 pps, Make/Break = 40/60 R2: pulse mode with 20 pps, Make/Break = 33/66 R3: pulse mode with 10 pps, Make/Break = 40/60 R4: pulse mode with 10 pps, Make/Break = 33/66 C1: pulse mode with 10 pps, Make/Break = 33/66 and temp. DTMF with 87 ms DTMF burst, 140 ms pause MODE pin pulled to R4: with temporary DTMF, 87 ms DTMF burst and 87 ms pause	MODE MODE
39	DP	Pulse dialing output. Flash key will cause \overline{DP} to be active in either DTMF mode or pulse mode. In on-hook state is \overline{DP} = VDD	
40	Mask	Short mute during pulse dialing, active high During MASK an internal NPN transistor shortens VL against VI.	MASK
41	R1		
42	R2		0
43	R3		
44	R4	Keyboard input	

Keyboard Operation

,	C1	C2	C3	C4		
-	1	2	3	S S	N/1	
-	I	2	3	3	M1	
	4	5	6	×	M2	R2
_	7	8	9	Α	M3	R3
-	*/T	0	#	R/P	N	R4
$\perp \leftarrow$	F1	F2	F3	E	1	
		 R/P: Redial ar N: Notice function */T: * function 	ertory dialing functi nd pause function k ction ; pulse-to-tone funct e-touch memory	ey)	
Normal Dia	ling	2. Dialing length	, D [.] n will be dialed out. is unlimited, but rec ngth oversteps 32 di	dial is inhibited if I	•	-
Redialing		OFF HOOK , HOOK , R/P	D1 , D2 ,	, Dn BUSY	Y, Come ON	HOOK ,OFF
		otherwise, it exect	execute the redial fu utes the pause func lial memory: 0 to 9,	tion (3.6 s).	-	
		memory. Characters F1, F	2, F3, Earth, (* in p 2, F3, Earth, (* in put was stopped, wh	pulse mode) wi	Il not be dialled	l out from redial
		Example:				
		OFF/ HOOK, D1,	D2, F1, D4, D5, S, S	S, M1		
		a) ON/OFF-HOOk b) ON/OFF-HOOk		1, D2 will be diale 2, F1, D4, D5 will		ng out stops
			nemory can be cop memory (except re			





	Example:	
	OFF/ HOOK, D1, D2, Dn	
	a) ON/OFF-HOOK, R/P, N. b) ON/OFF-HOOK, R/P, S, S, Mn (or Ln)	D1, Dn copied to N D1, Dn copied to Mn (or Ln)
	but	
	OFF/ HOOK, M1	content of M1 will be dialed out
	a) ON/OFF-HOOK, R/P, S, S, M2 b) ON/OFF-HOOK, M1, S, S, M2	not possible, M2 will be erased not possible, M2 will be erased
Number Store	OFF HOOK , D1 , D2 ,, Dn , S 1. D1, D2,, Dn will be stored in memo dialed out.	S , S , Mn (or Ln) ry location only (not in redial memory) and
	OFF HOOK S , D1 , D2 ,, Dn	, S , Mn (or Ln)
	store mode, R/P is the pause function	ry location but will not be dialed out. digit in memory, also F1, F2, F3, Earth. In n key; */T is the pulse-to-tone function key. store function is executed or when the state
	of the hook switch is changed.	
	5. Number store can be linked without ge	oing ON/OFF-Hook
	Example:	
	OFF/HOOK S, D1, D2, Dn, S, M1	storing D1, D2, Dn to M1
	S, D1', D2', Dn', S, M	I2 storing D1', D2', Dn' to M2
Repertory Dialing	1. OFF HOOK , Mn 2. OFF HOOK , A , Ln	
Notice (N)	OFF HOOK D1 , D2 ,, D	Dn , N
	, , ,	ressing the N key will cause D1 to Dn to be
	2. Pressing key N again, after D1, D2, again	Dn was copied to N, N will be dialed out
	OFF HOOK , N	
	3. D1 to Dn will be dialed out after the N	
	4. Notice function is valid as first key only	y.
Cascaded Dialing	1. Normal dialing + Repertory dialing + N	Normal dialing
	2. Repertory dialing + Normal dialing + N	-
	3. Redialing + Normal dialing + Repertor	ry dialing
	4. Redialing is valid as first key-in only.	

Figure 3. Pulse Mode Normal Dialing

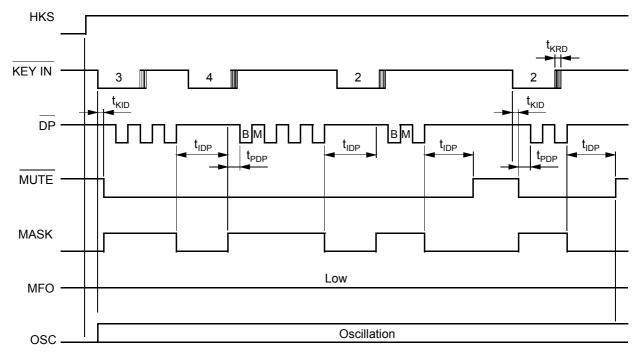
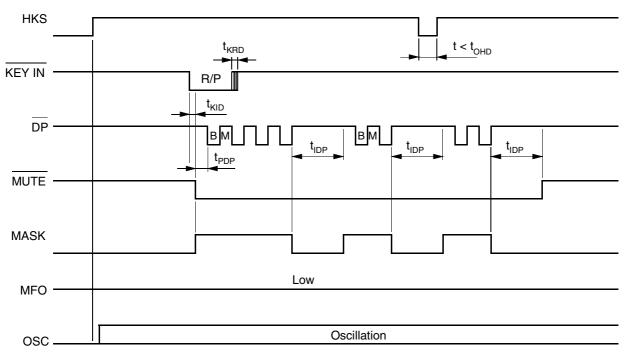
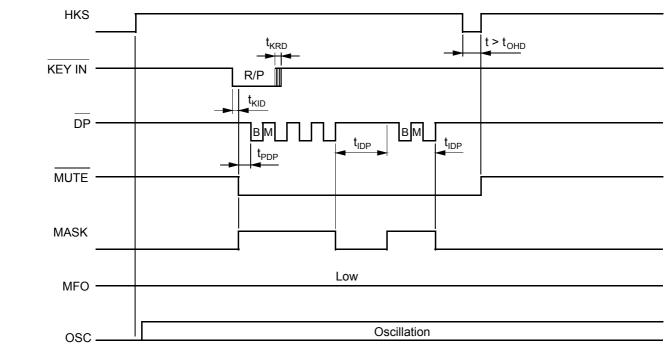


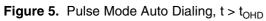
Figure 4. Pulse Mode Auto Dialing, t < t_{OHD}













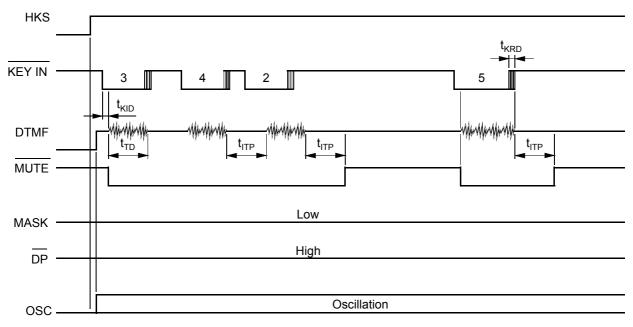


Figure 7. DTMF Mode Auto Dialing (t < t_{OHD})

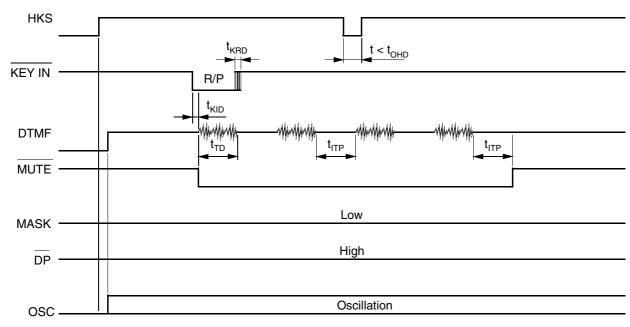
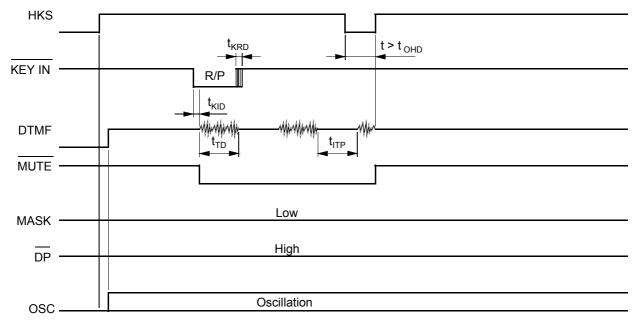


Figure 8. DTMF Mode Auto Dialing (t > t_{OHD})

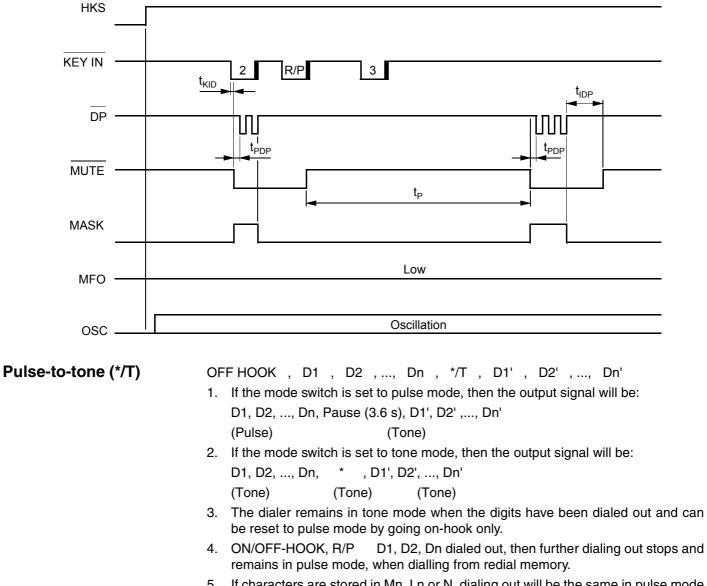


Access Pause

- OFF HOOK , D1 , D2 , R/P , D3 ,..., Dn'
- 1. The pause function can be stored in the memory.
- 2. The pause function is executed in normal dialing and redialing.

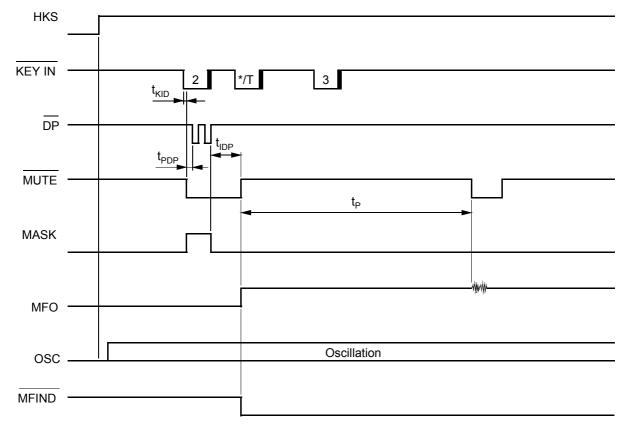
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Figure 9. Pause Function



5. If characters are stored in Mn, Ln or N, dialing out will be the same in pulse mode as point 1.

Figure 10. Pulse-to-tone Operation



Flash (F1 or F2 or F3)

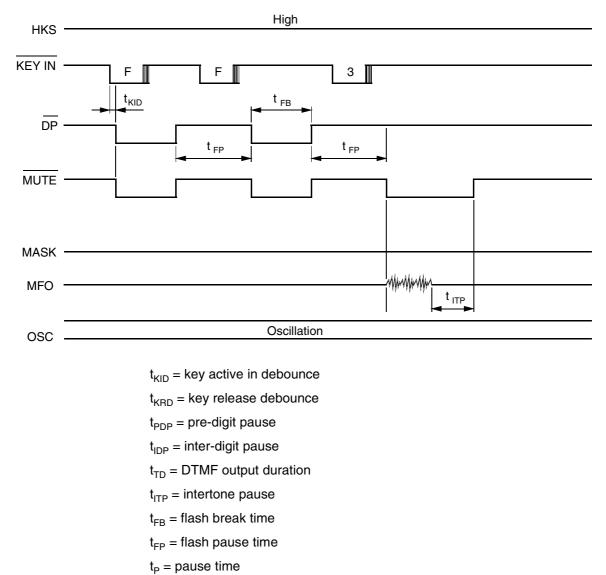
OFF HOOK , Fn

- 1. The dialer will execute a flash break and the entire flash pause time will elapse before the next digits are dialed out.
- 2. The flash key can be stored as a digit in the memory. Only one flash, however, will be released to the users.
- 3. The system will return to the initial state after the flash pause time has elapsed.

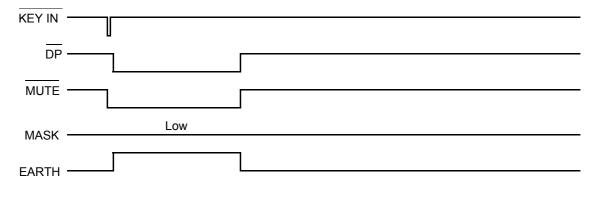


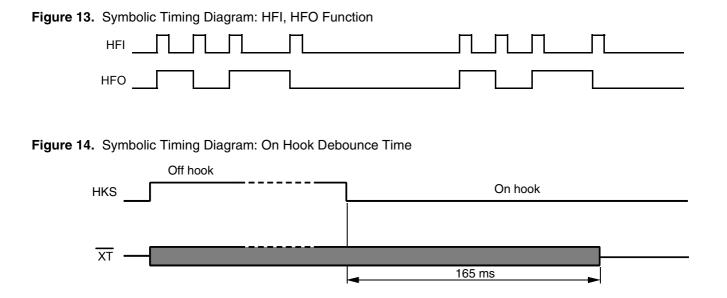
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Figure 11. Flash Operation

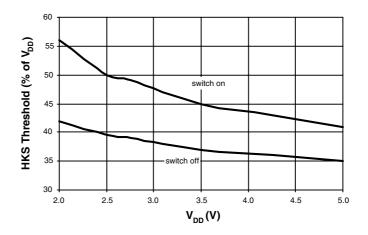
















Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Parameters	Symbol	Value	Unit
Line current	Ι _L	140	mA
DC line voltage	VL	14	V
DC voltage at pins 1 to 11 and 33 to 44	V _{DC}	5.5	V
Junction temperature	Тj	125	°C
Ambient temperature	T _{amb}	-25 to +75	°C
Storage temperature	T _{stg}	-55 to +150	°C
Total power dissipation, $T_{amb} = 60^{\circ}C$, SSO44	P _{tot}	0.9	W
Junction ambient, SSO44	R _{thJA}	70	K/W

Note: ESD withstand voltage 1 kV according to ESD standard S5.1 (HBM)

Electrical Characteristics: Speech Circuit

Reference point pin GND, f = 1000 Hz, 0 dBm = 775 mV_{rms}, R_{DC} = 39 Ω /1 W, T_{amb} = 25°C, unless otherwise specified, refer to "Basic Test Circuit". CLIM = GND

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Line voltage	$I_{L} = 8 \text{ mA}$ $I_{L} = 20 \text{ mA}$ $I_{L} = 73 \text{ mA}$ $I_{L} = 100 \text{ mA}$	VL	3.6 5.9 6.9	1.4 3.85 6.55	4.1 7.2 8.2	V V V V
Transmit and Sidetone	•	•	•	•	•	•
Input resistance	R _i	R _i	45	80	120	kΩ
Gain	I _L = 20 mA, S5 = open	Gs	46.8	47.8	48.8	dB
Gain change with current	$I_L = 20$ to 60 mA, $R_{AGC} = infinite$	ΔG_S	-0.5		0.5	dB
Gain deviation	$T_{amb} = -10 \text{ to } +60^{\circ}\text{C}, I_{L} = 20 \text{ mA}$	ΔG_S	-0.5		0.5	dB
Line-loss compensation	$R_{AGC} = 12 \text{ k}\Omega, I_L = 73 \text{ mA}$	ΔG _s	-7	-6	-4.8	dB
Distortion at line $V_L = 0.775 V_{rms}$	I _L = 20 mA, S5 = open	d _t			2	%
Maximum output voltage at line $d \le 5\%$	$I_L = 20 \text{ mA}, V_{mic} = 10 \text{ mV},$ CLIM = 2.2 µF, S ₁ = open	V _{Lmax}		1.2		dBm
Attack time transmit anticlipping	CLIM = 2.2 μF	t _{att}		3.5		ms
Noise at line weighted psophometrically	I _L > 20 mA, G _S = 48 dB	n _o			-72	dBmp
Sidetone reduction	$I_L \ge 20 \text{ mA}$	G _{STA}	10	15	20	dB
DTMF Amplifier	•	•	•	•	•	•
Volume range d < 5%	Single tone, $I_L \ge 20 \text{ mA}$	VL	1.3			dBm
DTMF output level low frequency group	$I_{L} = 20 \text{ mA}, \text{ S5} = \text{closed}$ $T_{\text{amb}} = -5^{\circ}\text{C} \text{ to } +60^{\circ}\text{C}$	VL	-7.6		-4.6	dBm
Pre-emphasis between high- and low-level frequency group	$P_{PRE} = P_{HLG} - P_{LLG} S5 = closed,$ $T_{amb} = -5^{\circ}C \text{ to } +60^{\circ}C$	P _{PRE}	1.9	2.5	3.1	dB
Total harmonic distortion relative to sum level of low and high frequency group signal	IL \ge 20 mA, measured at pin MFO	THD		-33	-25	dBr

Electrical Characteristics: Speech Circuit (Continued)

Reference point pin GND, f = 1000 Hz, 0 dBm = 775 mV_{rms}, R_{DC} = 39 Ω /1 W, T_{amb} = 25°C, unless otherwise specified, refer to "Basic Test Circuit". CLIM = GND

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Receiving Amplifier		L.	1		1	
Gain	$I_L \ge 20 \text{ mA}$	G _R	3		5	dB
Gain change with current	$I_L = 20 \text{ to } 60 \text{ mA}$ $R_{AGC} = \text{infinite}$	ΔG_{R}	-0.5		0.5	dB
Gain deviation	$T_{amb} = -10 \text{ to } +60^{\circ}\text{C}$ $I_{L} = 20 \text{ mA}$	ΔG_{R}	-0.3		0.7	dB
Line-loss compensation	I _L = 73 mA	DG _R	-7	-6	-4.7	dB
Receiving noise at earphone weighted psophometrially	I _L = 73 mA	n _i		-77.5	-71	dBm
Gain change when muted	$I_L \ge 20 \text{ mA}$	G _{RM}	24	29	34	dB
Output voltage push-pull	I _L \ge 20 mA, Z _{ear} = 68 nF, 100 Ω in series, d \le 2%	V _{RECO}	0.8	0.9		V _{rms}
Ear protection differential	I _L = 40 mA, V _{gen} = 4 V _{rms} , Z _{ear} = 68 nF + 100 Ω	V _{ear}	1.3	1.6	2.5	V _{rms}
Supply Voltage (For Internal Use C	Dnly)		•	•	•	•
Output voltage Note: Output must be limited externally to 5.5 V maximum	$I_L \ge 20$ mA dialing mode	V _{DD}	2.0		6.3	v
Available current for peripherals	$I_L \ge 20$ mA dialing mode	I _{DD}	150			μA
Transmit	·					
Maximum output voltage swing at line	$I_L = 20 \text{ mA}, V_{MIC} = 50 \text{ mV}_{rms}$	V _{L max}		3.4	4	Vpp
Mute suppression transmit with privacy function	I _L = 20 mA	G _{SPRIV}	60			dB

DC Characteristics Dialer

 V_{DD} = 2.7 V, f_{OSC} = 3.58 MHz, all outputs unloaded, S9 closed; HKS = 1

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Memory retention current	HKS = 0, V _{DD} = 1.0 V	I _{MR}			0.1	μA
Data retention voltage				0.5		V
DTMF distortion	$R_L = 5 k\Omega$	d		-30	-23	dB
DP output sink current	V _{PO} = 0.5 V	I _{PL}	0.5			mA
Keyboard input drive current	V ₁ = 0 V	I _{KD}		20		μA
Keyboard input sink current	V ₁ = 2.7 V	I _{KS}		500		μA
Key on resistance		R _{KON}			5	kΩ
Key off resistance		R _{KOFF}	100			kΩ
Mask sink/drive current		I _M H/L	0.5			mA
Earth sink/drive current		I _e H/L	0.5			mA





DC Characteristics Dialer (Continued)

V_{DD} = 2.7 V, f_{OSC} = 3.58 MHz, all outputs unloaded, S9 closed; H	IKS = 1
--	---------

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Isolation resistance XT/XT		Riso	4.7			MΩ
Maximum voltage at HKS					5.5	V
Maximum input current at HKS					0.5	mA

AC Characteristics Dialer

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Keypad active in debounce mode		t _{KID}	15	20	25	ms
Key release debounce		t _{KRD}	15	20	25	ms
Dre dieit neuro	MODE pin = R3 (10 pps) MODE pin = C1, C4 (10 pps)	t _{PDP} t _{PDP}	37 31	40 33.3	41 33.5	ms ms
Pre-digit pause	MODE pin = R1 (20 pps) MODE pin = R2	t _{PDP} t _{PDP}		20 16.65		ms ms
Inter-digit pause (auto dialing)	10 pps, $t_{IP} = t_{IDP} + t_{PDP}$ 20 pps	t _{IP} t _{IP}	810	836 512	860	ms ms
Make/break ratio	MODE pin = R1 (20 pps), R3 10 pps) MODE pin = C1, R4 (10 pps) R2	M/B	40.8:60.2	40:60	39.2:60.8	%
DTMF output duration	(20 pps) Auto dialing, MODE = C4 MODE = C3	t _{TD}	35.6:64.4 84 84	33:67 87 87	31.2:68.8 90 90	% ms
Inter-tone pause	Auto dialing, MODE = C4 MODE = C3	t _{ITP}	84 135	87 140	90 147	ms
Flash break time F1 F2 F3	C_1 connected to GND C_2 connected to GND C_3 connected to GND	t _{FB}	95 245 590	98 250 604	101 255 610	ms ms ms
Rise time of leading edge at HKS	20 to 70% of VDD	t _{rHKS}			10	ms
Flash pause time	F1, F2, F3	t _{FP}	0.9	1	1.1	S
Pause time		t _P	3.5	3.6	3.7	S
On-hook debounce time		t _{ohd}	145	165	185	ms
Earth time	C ₄ connected to GND	t _{et}		604		ms
Earth pause time		t _{pt}	0.9	1	1.1	S
Break duration	MODE pin = R3 MODE pin = C1, R4	t _B	57.6 63	60 66.7	62.4 69	ms ms
	MODE pin = R1 (20 pps) MODE pin = R2	t _B		30 33.35		ms ms
Make duration	MODE pin = R3 MODE pin = C1, R4	t _M	38 31	40 33.3	41 35	ms ms
	MODE pin = R1 (20 pps) MODE pin = R2	t _M		20 16.65		ms ms
Prock - make duration	MODE pin = C1, R3, R4	t _P	95	100	105	ms
Break + make duration	MODE pin = R1, R2 (20 pps)	t _P		50		ms

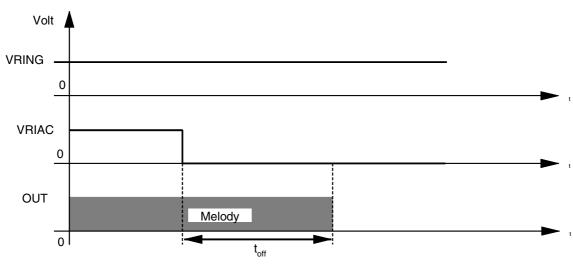
Electrical Characteristics Tone Ringer

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Supply current, outputs open	V _{RIAC} = 20 V	I _{RING}	2.1		3.8	mA
Switch-on threshold	V _{RIAC} , THA = open	V _{RON}	8	9	10	V
Switch-off threshold	V _{RIAC}	V _{ROFF}	5.0	5.6	6.5	V
Ringing frequency	$\label{eq:R} \begin{array}{l} R = 150 \ \mathrm{k}\Omega, \ C = 1 \ \mathrm{nF} \\ V_{RIAC} > V_{RON} \end{array}$	f _{1H} f _{1L}	937 752	1010 808	1083 868	Hz Hz
Range of external components for		С	1000		2200	pF
R/C oscillator		R	50		330	kΩ
Audio sequence frequency		f ₂	11.5	12.5	14.0	Hz
Output voltage swing	$V_{\text{Ring}} = 25 \text{ V}, \text{ C}_{\text{out}} = 68 \text{ nF}$	V _{out}	21	23		V _{pp}
Turn-off delay	See Figure 15	t _{off}		65	100	ms

£ – 4 kHz V. - 25°C reference point GND unless otherwise specified _ 00 V/ T

Note: Max. current into internal zener diode at pin VRING = 20 mA

Figure 16. Turn-off Delay Time



Note

The oscillator frequency is defined by R and C at pin RCK.

$$f_{Osc} \approx \frac{I}{1.594 \times C \times [R + 3809 \Omega]}$$

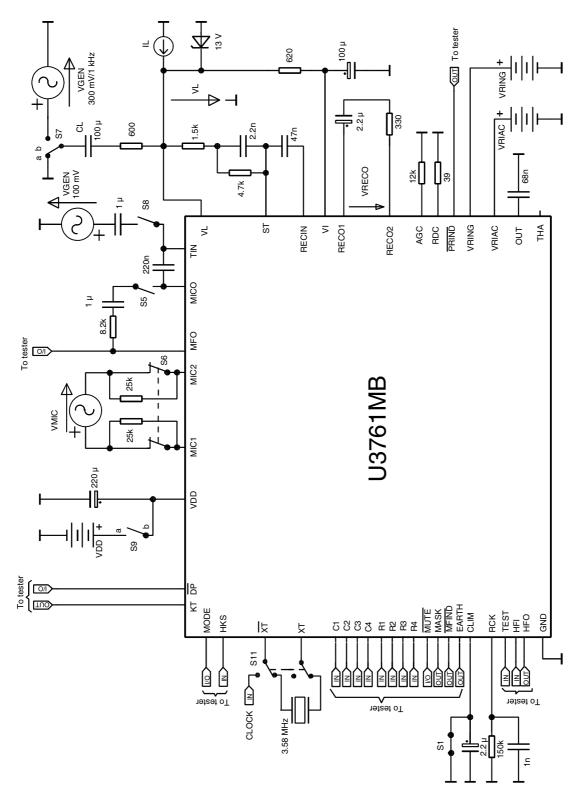
The audio sequence frequency f_2 and the ratio of low frequency f_{1L} and high frequency f_{1H} are derived from the oscillator by internal deviders. So f_2 , f_{1H} and f_{1L} are given by:

$$f_2 = \frac{f_{Osc}}{320}$$
; $f_{1H} = \frac{f_{Osc}}{4}$; $f_{1L} = \frac{f_{Osc}}{5}$

For more information on adjusting ringer melody refer to the document "Application and Adjustment Hints".

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Figure 17. Basic Test Circuit



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Equations for Electrical Characteristic Parameters of the Speech Circuit

The equations refer to the basic test circuit. If not otherwise specified, the switches in the basic test circuit are inactive.

Transmit Gain

$$GS = 20 \times log \left(\frac{V_L}{V_{MIC}}\right)$$

 $V_{MIC} = 3 \text{ mV}/1 \text{ kHz}, S5 = \text{open}$

Line-loss Compensation Transmit

 Δ GS = GS (at I_L = 73 mA) - GS (at I_L = 20 mA) TX-mode: V_{MIC} = 3 mV/1 kHz, S5 = open

Line-loss Compensation Receive

 Δ GR = GR (at I_L = 73 mA) - GR (at I_L = 20 mA) RX-mode: V_{gen} = 300 mV/1 kHz, S7b

Receiving Gain

 $GR = 20 \times log\left(\frac{V_{RECO}}{V_{L}}\right)$

RX-mode: V_{gen} = 300 mV/1 kHz, S7b

Sidetone Reduction

 $GSTA = 20 \times log \left(\frac{V_L}{V_{RECO}} \right) \text{ (in TX-mode) + GR}$

TX-mode: V_{MIC} = 3 mV/1 kHz, S5 = open

Input Impedance of Microphone Amplifier

 $Ri = \frac{50 \text{ k}}{\left(\frac{V_{L(S6 = closed)}}{V_{L(S6 = open)}} - 1\right)}$

TX-mode: VMIC = 3 mV/1 kHz, S5 = open

Gain Change when Muted

$$\begin{split} \text{GRM} &= 20 \times \text{log}\Big(\frac{\text{V}_{\text{RECO}}}{\text{V}_{\text{L}}}\Big) \ (\text{Mute} = \text{inactive}) - 20 \times \text{log}\Big(\frac{\text{V}_{\text{RECO}}}{\text{V}_{\text{L}}}\Big) \ (\text{Mute} = \text{active}) \\ \text{V}_{\text{gen}} &= 100 \text{ mV/1 kHz}, \text{S5} = \text{open}, \text{S8} = \text{open} \end{split}$$

Total Harmonic Distortion (THD)

$$THD = 20 \times log \left(\frac{\sqrt{n_1 \times U_{LG}^2 + n_1 \times U_{HG}^2 + n_2 \times U_{LG}^2 + n_2 \times U_{HG}^2 + ...n_n \times U_{LG}^2 + n_n \times U_{HG}^2}{\sqrt{U_{LG}^2 + U_{HG}^2}} \right)$$

 $n_1, ..., n_n$ = harmonics of high and low frequency group

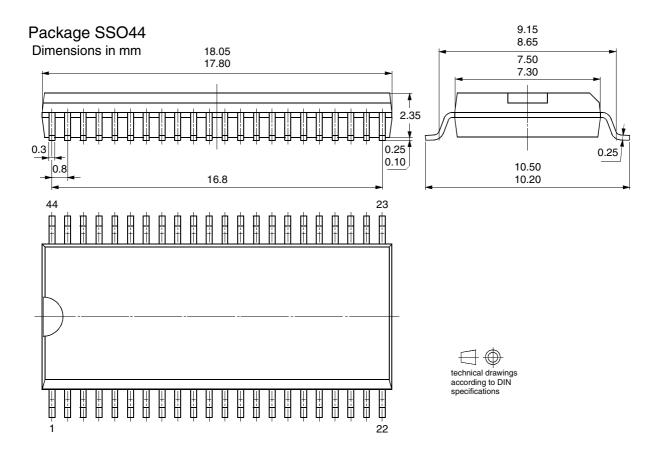
4744A-CORD-09/03



Ordering Information

Extended Type Number	Package	Remarks
U3761MB-TFN	SSO44	Tube
U3761MB-TFNG3	SSO44	Taped and reeled

Package Information





Atmel Corporation

2325 Orchard Parkway San Jose, CA 95131, USA Tel: 1(408) 441-0311 Fax: 1(408) 487-2600

Regional Headquarters

Europe

Atmel Sarl Route des Arsenaux 41 Case Postale 80 CH-1705 Fribourg Switzerland Tel: (41) 26-426-5555 Fax: (41) 26-426-5500

Asia

Room 1219 Chinachem Golden Plaza 77 Mody Road Tsimshatsui East Kowloon Hong Kong Tel: (852) 2721-9778 Fax: (852) 2722-1369

Japan

9F, Tonetsu Shinkawa Bldg. 1-24-8 Shinkawa Chuo-ku, Tokyo 104-0033 Japan Tel: (81) 3-3523-3551 Fax: (81) 3-3523-7581

Atmel Operations

Memory 2325 Orchard Parkway San Jose, CA 95131, USA Tel: 1(408) 441-0311 Fax: 1(408) 436-4314

Microcontrollers 2325 Orchard Parkway San Jose, CA 95131, USA Tel: 1(408) 441-0311 Fax: 1(408) 436-4314

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1150 East Cheyenne Mtn. Blvd. Colorado Springs, CO 80906, USA Tel: 1(719) 576-3300 Fax: 1(719) 540-1759

Scottish Enterprise Technology Park Maxwell Building East Kilbride G75 0QR, Scotland Tel: (44) 1355-803-000 Fax: (44) 1355-242-743 RF/Automotive

Theresienstrasse 2 Postfach 3535 74025 Heilbronn, Germany Tel: (49) 71-31-67-0 Fax: (49) 71-31-67-2340

1150 East Cheyenne Mtn. Blvd. Colorado Springs, CO 80906, USA Tel: 1(719) 576-3300 Fax: 1(719) 540-1759

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